

1. Scope :

This specification applies to silicon zerocrossing phototriac chips,
Device No. ST-0182S

2. Structure :

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

3. Size :

- 3-1. Chip size : 42.5 mils × 42.5 mils (1.080 mm ×1.080mm).
- 3-2. Chip thickness : 12 ± 1.0 mil (0.305 ± 0.025 mm).
- 3-3. Pad area : 5.5 mil × 4.7 mil (0.140 mm ×0.120 mm).
- 3-4. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	I_{DRM}	$V_{DRM}=800V$			500	nA
Peak on-state voltage	V_{TM}	$I_{TM}=100mA$		1.6	3	V
Critical rate of Rise voltage	dv/dt		1000			V/ μ S
Holding current	I_H			200		μ A
Inhibit Voltage	V_{INH}	$I_{DS}=10\mu A$		10	20	V

